isc Silicon NPN Power Transistor 2SC3422

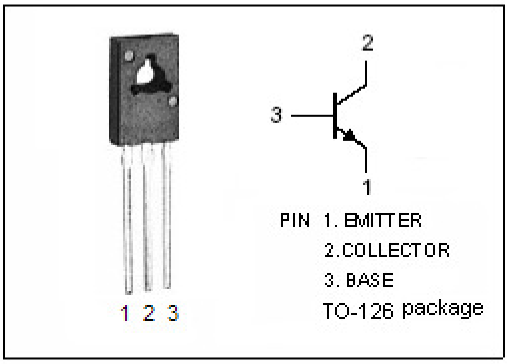
DESCRIPTION

·Collector-Emitter Breakdown Voltage

: $V_{(BR)CEO}$= 40V(Min)

·Good Linearity of h_{FE}

·Complement to Type 2SA1359

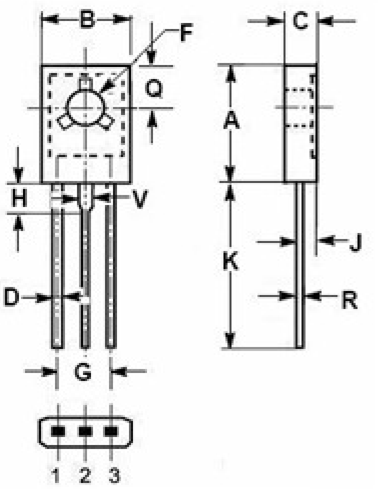


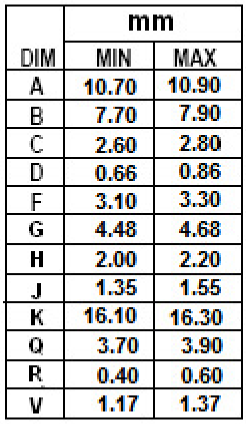
APPLICATIONS

·Audio frequency power amplifier

·Low speed switching

·Suitable for output stage of 5 watts car radio and car stereo





DIM	mm MIN	mm MAX
A	10.70	10.90
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	16.10	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ T_C=25℃	10	W
	Collector Power Dissipation @ T_a=25℃	1.5	

T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B=0.2A			0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.5A ; V_{CE}= 2V			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V; I_E= 0			0.1	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	μ A
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 2V	80		240	
h_{FE-2}	DC Current Gain	I_C= 2.5A; V_{CE}= 2V	25			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 2V		100		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V, f_{test}= 1MHz		35		pF

◆ h_{FE-1} Classifications

O	Y
80-160	120-240